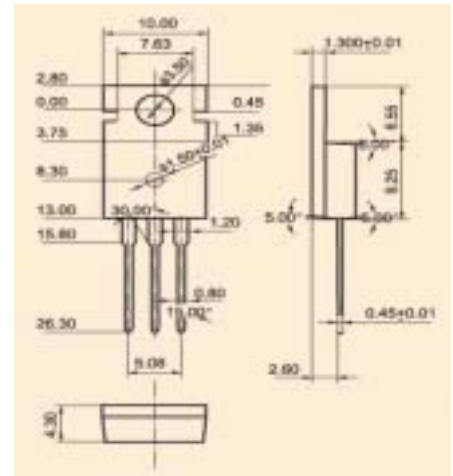


Silicon PNP Transistors



- . With TO-220 package
- . Complementary to 2SC2562

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	-60	V
V_{CEO}	Collector to emitter voltage	-50	V
V_{EBO}	Emitter to base voltage	-5	V
I_B	Base current		A
I_C	Collector current	-5	A
P_C	Collector power dissipation	25	W
T_j	Junction temperature	150	°C
T_{stg}	Storage temperature	-55~150	°C



TO-220

SYMBOL	PARAMETER	CONDITIONS	MIN	Typ	MAX	UNIT
I _{CBO}	Collector-base cut-off current	V _{CB} =-50V; I _E =0			-1	uA
I _{EBO}	Emitter-base cut-off current	V _{EB} =-5V; I _C =0			-1	uA
I _{CEO}	Collector-emitter cut-off current					
V _{CBO}	Collector-base breakdown voltage					
V _{(BR)ceo}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-50			V
V _{EBO}	Emitter-base breakdown voltage					
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =-8A; I _B =-0.15A		-0.2	-0.4	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =-1A; V _{CE} =-1V	70		240	
h _{FE-2}	Forward current transfer ratio	I _C =-3A; V _{CE} =-1V	30			
V _{BE(sat)1}	Base-emitter saturation voltages	I _C =-8A; I _B =-0.15A		-0.9	-1.2	V
V _{BE(sat)2}	Base-emitter saturation voltages					
C _{OB}	Collector Output Capacitance	V _{CB} =-10V; I _E =0;f=1MHz		70		pF
f _T	Transition frequency	I _C =-1A; V _{CE} =-4V		60		MHz